

GR2302

N-CHANNEL MOSFET

VOLTAGE	20 Volt	CURRENT	4 Ampere
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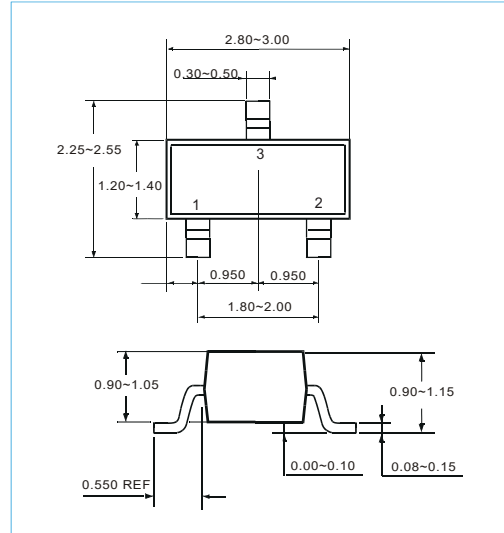
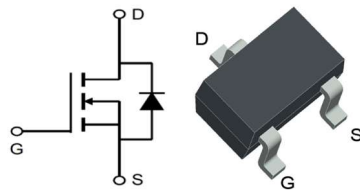
SOT-23 Unit:mm

FEATURES

- N-Channel Enhancement Mode Field Effect Transistor
- High dense cell design for extremely low Rds(on)
- Exceptional on-resistance and maximum DC current capability
- Lead free in compliance with EU RoHS

MECHANICAL DATA

- Case Material: Molded Plastic.
- UL Flammability Classification Rating 94V-0



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS T_A 25 C

SYMBOL	PARAMETER	VALUE	UNIT	
V _{DS}	Drain-Source Voltage	20	V	
V _{GS}	Gate-Source Voltage	±12	V	
I _D	Continuous Drain Current	T _C = 25°C	4	A
		T _C = 100°C	2.5	A
I _{DM}	Drain Current-Pulsed	10	A	
P _D	Power Dissipation	T _C = 25°C	1	W
R _{θJA}	Thermal Resistance from Junction to Ambient	125	°C/W	
T _J , T _{STG}	Operating and Storage Temperature Range	-50 to +150	°C	

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ELECTRICAL CHARACTERISTICS T_A 25 C

PARAMETER	SYMBOL	Test conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0 V, I _D =250 μA	20	22		V
Zero gate voltage drain current	I _{DSS}	V _{DS} =24V, V _{GS} =0V			1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±12V, V _{DS} =0V			±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	0.5	0.85	1.2	V
Drain-source on-resistance (note 1)	R _{DS(on)}	V _{GS} =4.5V, I _D =2.9A		30	45	mΩ
		V _{GS} =2.5V, I _D =2.5A		37	59	mΩ
Forward tranconductance (note 2)	g _{fs}	V _{DS} =5V, I _D =2.9A		8		S
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V, f=1MHz		300		pF
Output Capacitance	C _{oss}			120		
Reverse Transfer Capacitance	C _{rss}			80		
Total Gate Charge	Q _g	V _{DS} =10V, I _D =2.9A, V _{GS} =4.5V		4.0	10	nC
Gate-Source Charge	Q _{gs}			0.65		
Gate-Drain("Miller") Charge	Q _{gd}			1.2		
Turn-on delay time	t _{d(on)}	V _{DD} =10V, I _D =2.9A, R _{GEN} =6Ω, V _{GS} =4.5V		10	15	ns
Turn-on rise time	t _r			50	85	ns
Turn-off delay time	t _{d(off)}			17	45	ns
Turn-off fall time	t _f			10	20	ns
Maximum Continuous Drain to Source Diode Forward Current	I _S				4	A
Maximum Pulsed Drain to Source Diode Forward Current	I _{SM}				10	A
Drain to Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =2.9A		0.75	1.2	V

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

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Typical Characteristics

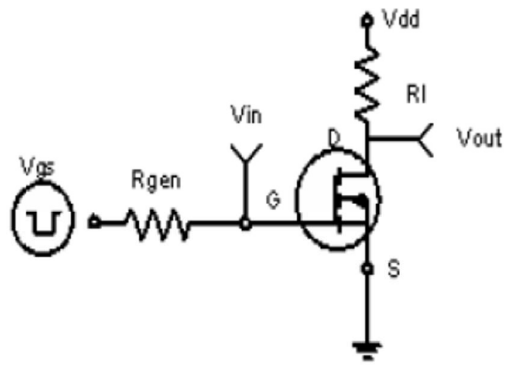


Figure1 :Switching Test Circuit

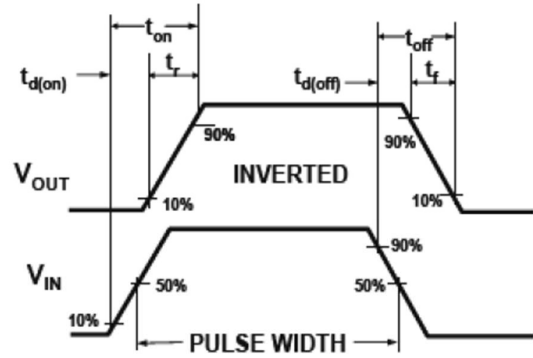


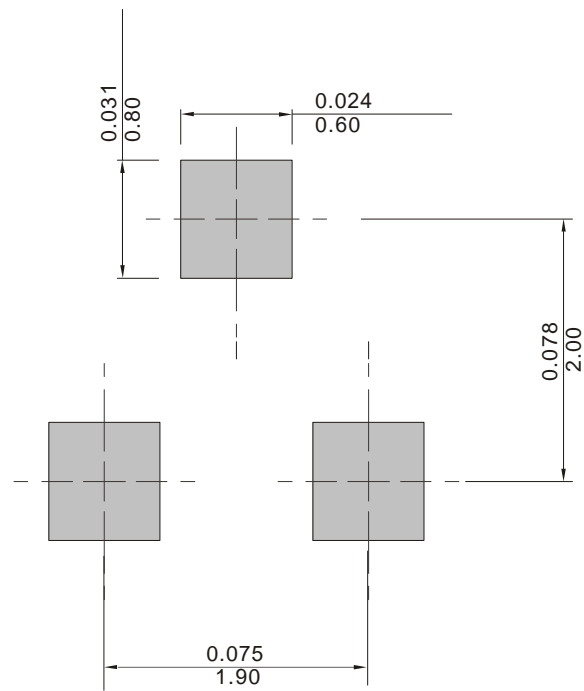
Figure2:Switching Waveforms

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MOUNTING PAD LAYOUT

SOT-23

Unit:Inch(mm)



ORDER INFORMATION

- Packing information

Part Number	Case	Reel Size	QUANTITY
GR2302	SOT-23	7 Inch	3000